

## PBSS5240Y,135 Datasheet

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DiGi Electronics Part Number PBSS5240Y,135-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBSS5240Y,135

Description TRANS PNP 40V 2A 6TSSOP

Detailed Description Bipolar (BJT) Transistor PNP 40 V 2 A 100MHz 430 m

W Surface Mount 6-TSSOP



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## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PBSS5240Y,135	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	2 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
40 V	350mV @ 200mA, 2A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	210 @ 1A, 2V
Power - Max:	Frequency - Transition:
430 mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
6-TSSOP, SC-88, SOT-363	6-TSSOP
Base Product Number:	
PBSS5240	

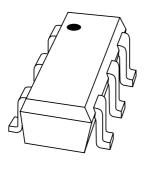
## **Environmental & Export classification**

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## PBSS5240Y 40 V low V<sub>CEsat</sub> PNP transistor

Product data sheet Supersedes data of 2001 Oct 24 2002 Feb 28



## 40 V low V<sub>CEsat</sub> PNP transistor

#### PBSS5240Y

#### **FEATURES**

- Low collector-emitter saturation voltage
- · High current capability
- Improved device reliability due to reduced heat generation
- Replacement for SOT89/SOT223 standard packaged transistors due to enhanced performance.

#### **APPLICATIONS**

- · Supply line switching circuits
- · Battery management applications
- DC/DC converter applications
- · Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

#### **DESCRIPTION**

PNP low  $V_{\text{CEsat}}$  transistor in a SOT363 (SC-88) plastic package.

NPN complement: PBSS4240Y.

#### **MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS5240Y	52*

#### Note

- 1. \* = p: made in Hongkong.
  - \* = t: made in Malaysia.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-40	٧
I <sub>CM</sub>	peak collector current	-3	Α
I <sub>C</sub>	collector current (DC)	-2	Α
R <sub>CEsat</sub>	equivalent on-resistance	<200	mΩ

#### **PINNING**

PIN	DESCRIPTION			
1	collector			
2	collector			
3	base			
4	emitter			
5	collector			
6	collector			

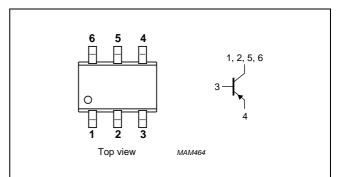


Fig.1 Simplified outline (SOT363; SC-88) and symbol.

## 40 V low V<sub>CEsat</sub> PNP transistor

PBSS5240Y

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	<b>-</b> 5	V
I <sub>C</sub>	collector current (DC)		_	-2	Α
I <sub>CM</sub>	peak collector current		-	-3	Α
I <sub>BM</sub>	peak base current		_	-300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	270	mW
		T <sub>amb</sub> ≤ 25 °C; note 2	-	430	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### **Notes**

- 1. Device mounted on a printed-circuit board, single side copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single side copper, tinplated and mounting pad for collector 1 cm<sup>2</sup>.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to	note 1	463	K/W
	ambient	note 2	291	K/W

#### Notes

- 1. Device mounted on a printed-circuit board, single side copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single side copper, tinplated and mounting pad for collector 1 cm<sup>2</sup>.

## 40 V low $V_{\text{CEsat}}$ PNP transistor

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#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	-100	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_C = 0$	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}$	300	_	
		$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}$	260	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -1000 \text{ mA}$	210	_	
		$V_{CE} = -2 \text{ V}; I_{C} = -2000 \text{ mA}$	100	-	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -100 \text{ mA}; I_B = -1 \text{ mA}$	_	-100	mV
	voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	-	-110	mV
		$I_C = -750 \text{ mA}; I_B = -15 \text{ mA}$	_	-225	mV
		$I_C = -1000 \text{ mA}; I_B = -50 \text{ mA}$	_	-225	mV
		$I_C = -2000 \text{ mA}; I_B = -200 \text{ mA}$	_	-350	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -2000 \text{ mA}; I_B = -200 \text{ mA}$	_	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V; } I_{C} = -100 \text{ mA}$	_	-0.75	V
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	40	pF
F <sub>T</sub>	transition frequency	$I_C = -100 \text{ mA}$ ; $V_{CE} = -10 \text{ V}$ ; $f = 100 \text{ MHz}$	100	_	MHz

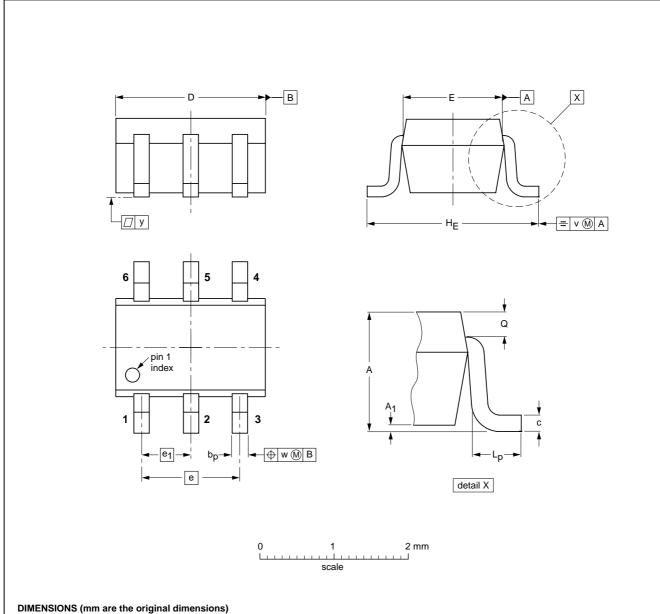
## 40 V low $V_{\text{CEsat}}$ PNP transistor

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

**SOT363** 



DIMENSIONS (	mm are the	original	dimensions)
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UNIT	Α	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	ø	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT363			SC-88			97-02-28

2002 Feb 28 5

#### 40 V low V<sub>CEsat</sub> PNP transistor

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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